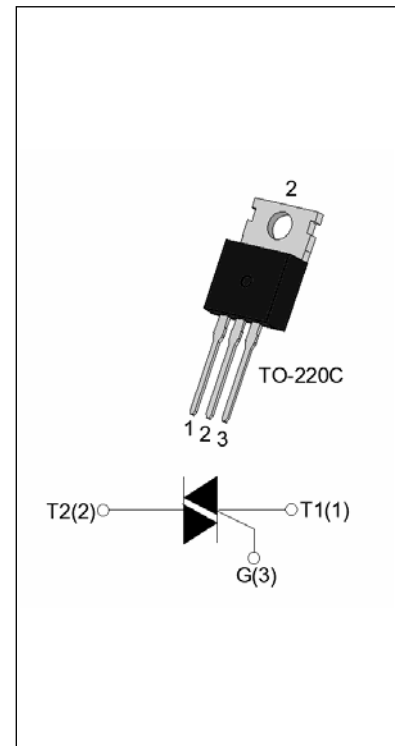


The T0620H-8C triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T0620H-8C provides a very high switching capability up to junction temperatures of 150°C. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	20/20/20	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 137^\circ\text{C}$)	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	60	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		66	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	18	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	80	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	3	kV
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(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	40	mA
				55	
I_H	$I_T=100mA$		MAX.	30	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	800	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs , $T_j=150$		MIN.	2	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	3	μs
t_{off}				30	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=8.5A t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.8	V
R_D	Dynamic resistance	$T_j=150$	63	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	1	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.7	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

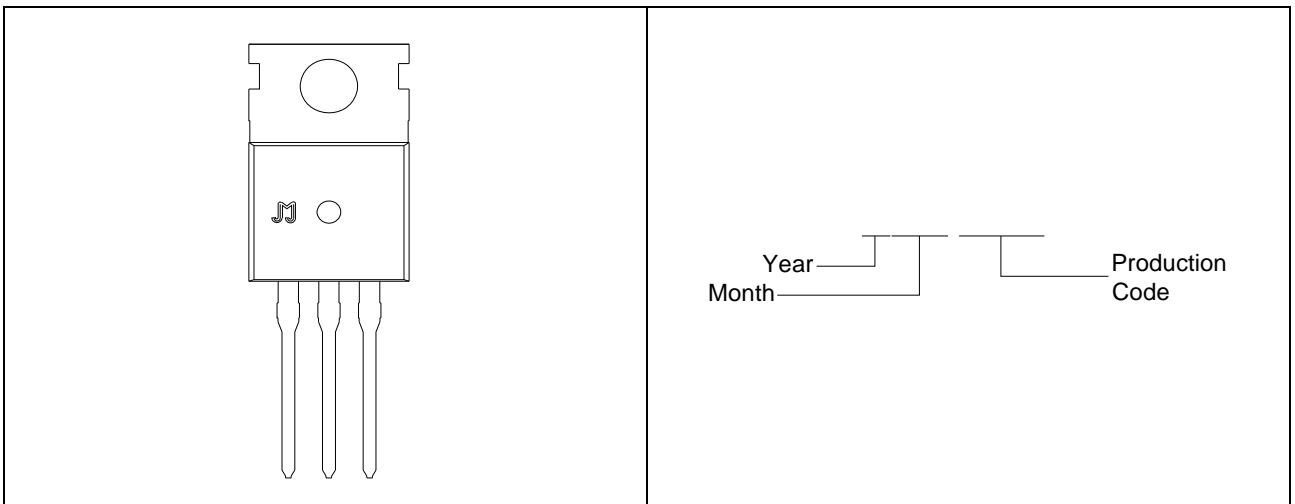
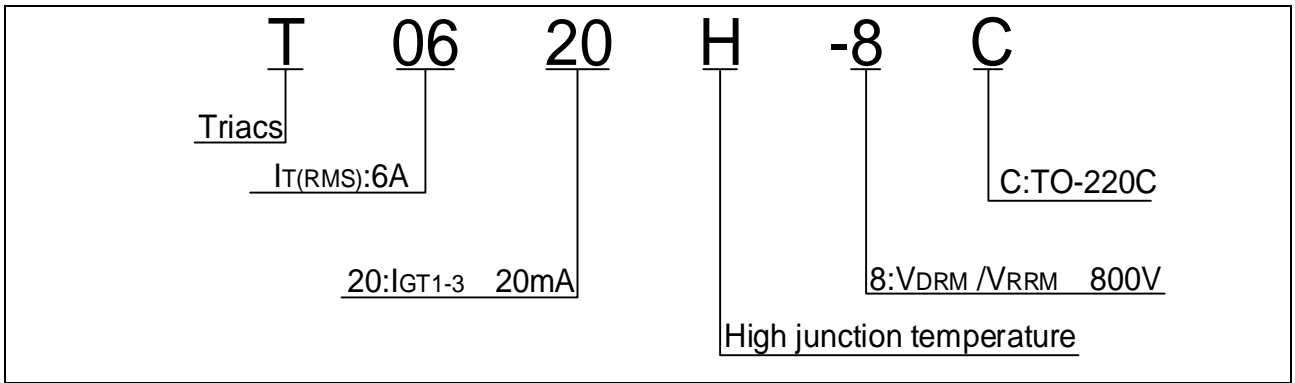


FIG.1 Maximum power dissipation versus RMS on-state current

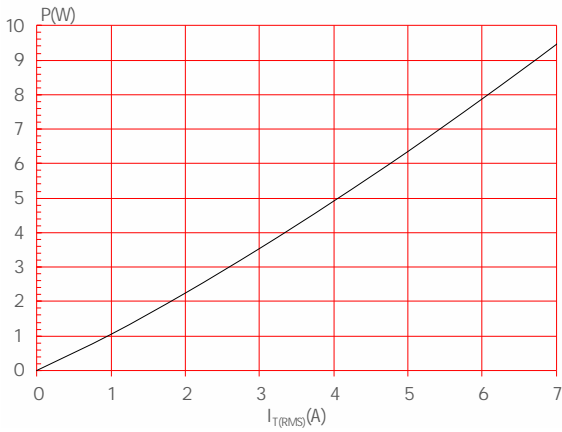


FIG.2: RMS on-state current versus case temperature

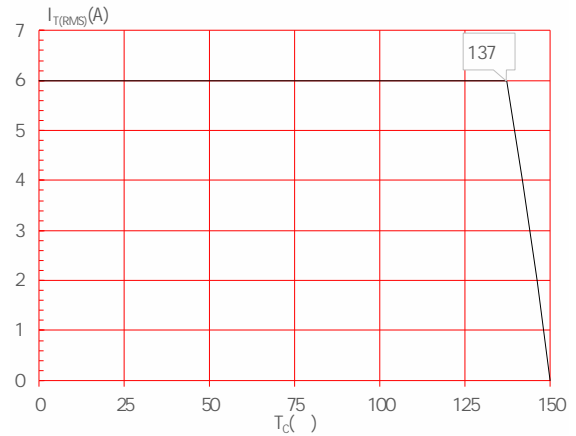


FIG.3: Surge peak on-state current versus number of cycles

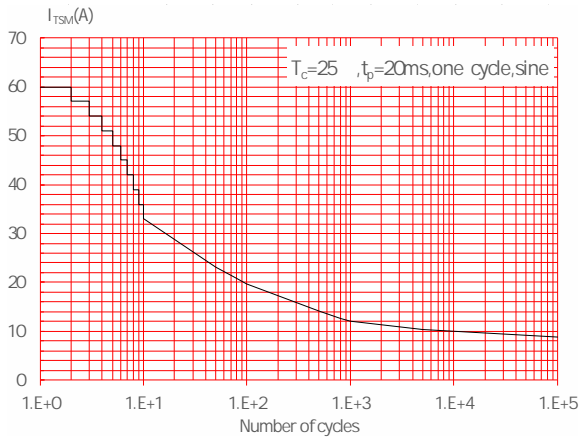


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 80\text{A}/\mu\text{s}$)

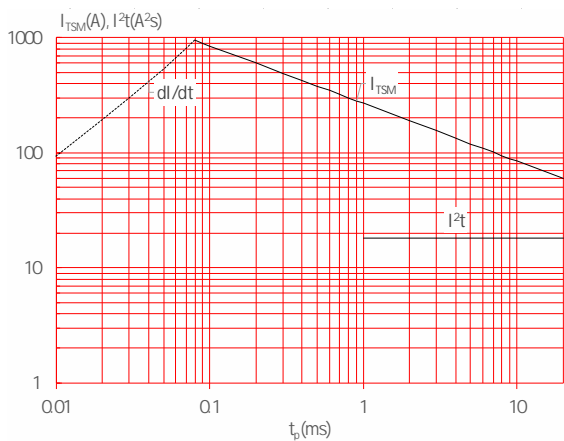


FIG.4: On-state characteristics

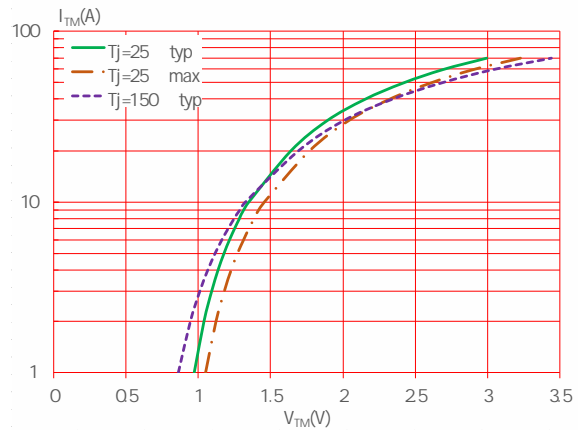


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

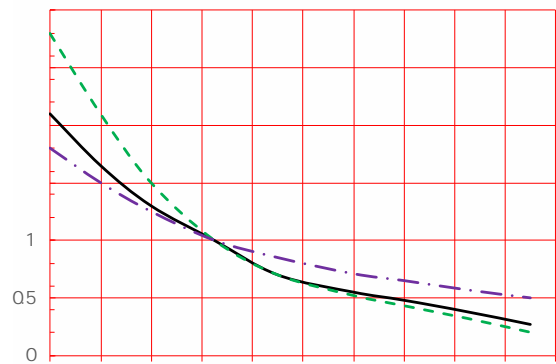
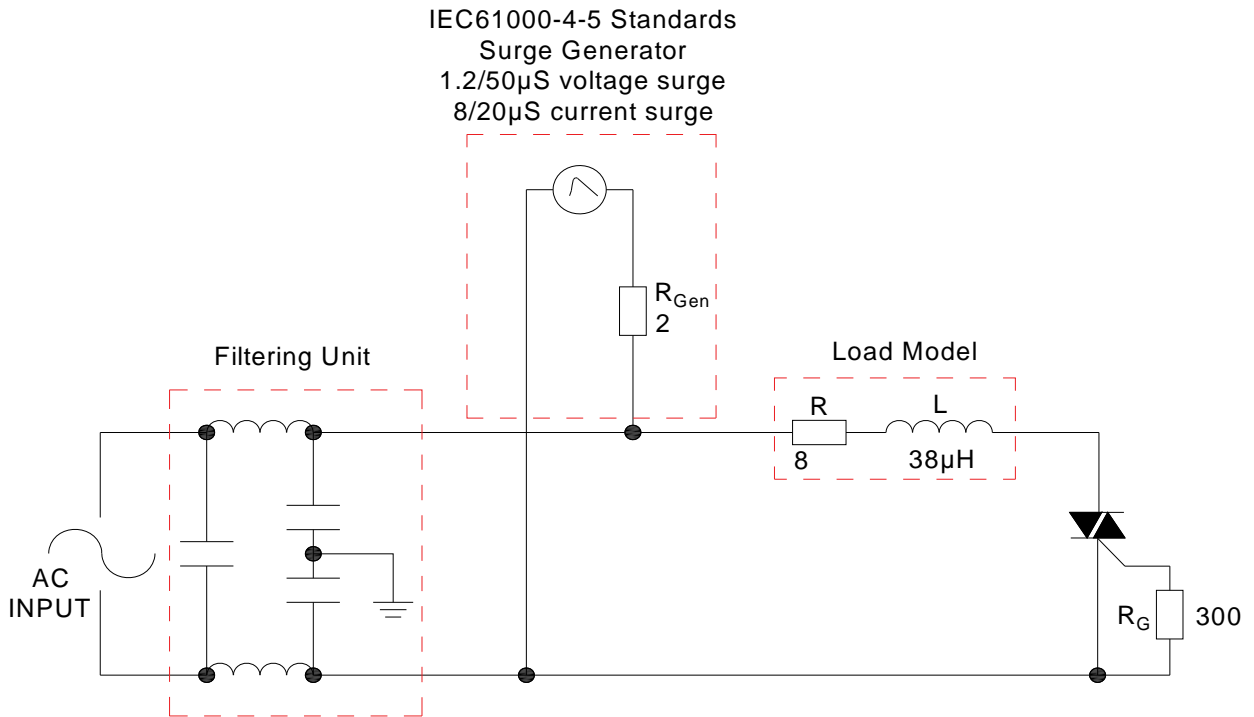


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie


Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T0620H-8C	800	20	TO-220C	50	Tube

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated

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